DFI500HF17DFRE1

1700V/500A Half Bridge IGBT Module

Description

The DFI500HF17DFRE1 offer lower losses and higher energy for soft switching applications.

.

Features

- 1700V500 A, V_{CE} (sat)(typ.) =1.8V
- Lower losses and higher energy
- Excellent short-circuit capability
- 62mm half bridge module

Applications

- Motor drive
- Inverter
- Power supply
- Wind Turbines

Circuit diagram

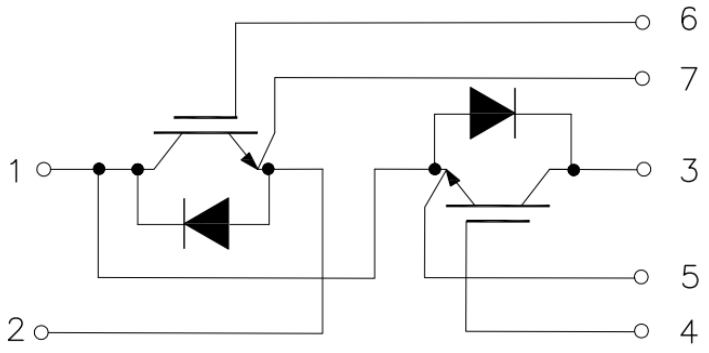

Figure 1. Out drawing & circuit diagram for DFI500HF17DFRE1

Pin Configuration and Marking Information

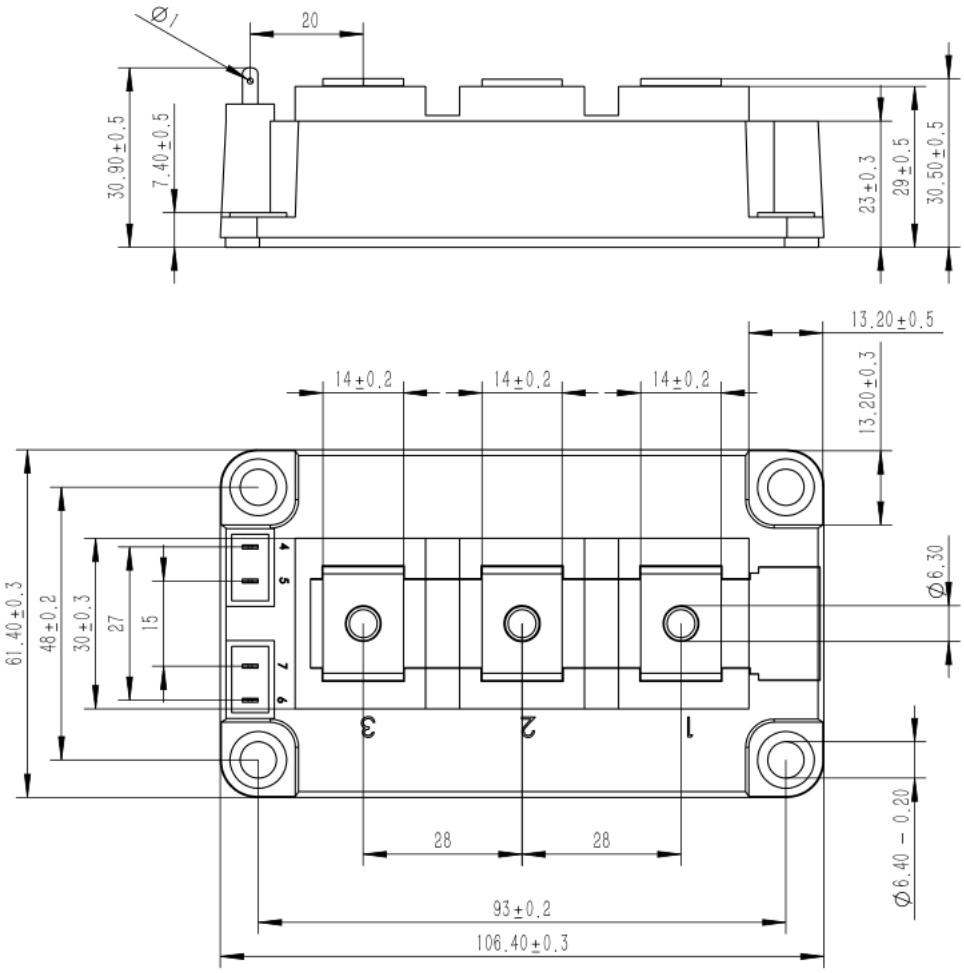

Figure 2. Pin configuration

Module

Parameter	Conditions	Value	Unit
Isolation Voltage	RMS, f = 50Hz, t =1min	4.0	KV
Material of module baseplate	-	Cu	-
Creepage distance	terminal to heatsink terminal to terminal	47 26	mm
Clearance	terminal to heatsink terminal to terminal	29 14	mm
CTI	-	>200	-
Module lead resistance, terminals – chip	T_C =25°C	0.8	mΩ
Mounting torque for module mounting	M6	3 to 6	Nm
Weight	-	315	g

Maximum Ratings (IGBT,T_j =25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-Emitter Voltage	G-E Short	1700	V
V_{GES}	Gate-Emitter Voltage	C-E Short	±20V	V
I_C	DC Continuous Collector Current	T_C =80°C	500	A
I_{CM}	Pulse Collector Current	t_p =1ms, Note1	1000	A
P_C	Maximum Power Dissipation	T_C =25°C, T_j =150°C(IGBT)	1645	W
I_F	Diode forward Current	-	500	A
I_{FRM}	Repetitive peak forward Current	t_p =1ms, Note1	1000	A
I^2t	I^2t-value	V_R =0V, t_p =10ms, T_j =125°C (Diode)	20000	A^2s
T_{jmax}	Max junction temperature	-	175	°C
T_{jop}	Operating junction temperature	-	-40 to 150	°C
T_{stg}	Storage temperature	-	-40 to 125	°C

Note1: Pulse width limited by maximum junction temperature

IGBT Electrical characteristics (T_j =25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C =500A, V_{GE} =15V	T_j =25°C	-	1.8	-	V
			T_j =125°C	-	2.2	-	V
			T_j =150°C	-	2.3	-	V
$V_{GE(th)}$	Gate-Emitter threshold Voltage	I_C =24mA, V_{CE} =V_{GE}		5.2	5.8	6.4	V
Q_G	Gate charge	V_{GE} = -15V to +15V		-	4.2	-	uC
R_{Gint}	Internal gate resistor	f=1M, Vpp=1V	T_j =25°C	-	2.55	-	Ω
C_{ies}	Input Capacitance	V_{CE} =25V, V_{GE} =0V, f =1MHz	T_j =25°C	-	33	-	nF
C_{oes}	Output Capacitance			-	1.2	-	nF
C_{res}	Reverse transfer Capacitance			-	0.5	-	nF
I_{CES}	Collector- Emitter Cut off Current	V_{CE} =1700V, V_{GE} =0V	T_j =25°C	-	-	1	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE} =20V, V_{CE} =0V	T_j =25°C	-	-	1.2	uA
$t_{d(on)}$	Turn-on delay time	V_{CC} =900V, I_C = 500A, V_{GE} =+15V/-8V, R_{Gon} = R_{Goff} =1Ω, Inductive load	T_j =25°C	-	240	-	ns
			T_j =150°C	-	244	-	
t_r	Rise time		T_j =25°C	-	84	-	ns
			T_j =150°C	-	102	-	
$t_{d(off)}$	Turn-off delay time		T_j =25°C	-	546	-	ns
			T_j =150°C	-	656	-	
t_f	Fall time		T_j =25°C	-	368	-	ns
			T_j=150°C	-	536	-	
E_{on}	Turn-on power dissipation		T_j =25°C	-	114	-	mJ
			T_j =150°C	-	177	-	

E_{off}	Turn-off power dissipation		T_j =25°C	-	103	-	mJ
			T_j =150°C	-	138	-	
I_{SC}	SC data	V_{GE}<15V V_{CC}=1000V	T_j =150°C t_p<10us	-	2000	-	A
$R_{th(j-c)}$	Thermal Resistance, Junction to Case (IGBT)			-	0.075	-	°C /W
$R_{th(c-s)}$	Thermal Resistance, Case to sink (Conductive Grease applied)			-	0.025	-	°C /W

Freewheeling Diode Electrical characteristics (T_j =25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V_F	Diode Forward Voltage	I_F =500A, V_{GE} =0V	T_j =25°C	-	1.82	-	V
			T_j =150°C	-	1.86	-	
t_{rr}	Diode Reverse Recovery Time	(Switch side) V_{CC} =900V, I_C =500A V_{GE} =+15V/-8V R_{Gon} = R_{Goff} =1Ω (FRD side) V_{rr}=900V, I_F=500A V_{GE}=+15V/-8V Inductive load switching operation	T_j =25°C		264		ns
			T_j =150°C		546		
I_{RM}	Peak reverse recovery Current		T_j =25°C	-	865	-	A
			T_j =150°C	-	742	-	
Q_{rr}	Recovered charge		T_j=25°C	-	132	-	uC
			T_j =150°C	-	155	-	
E_{rr}	Reverse recovered energy		T_j =25°C	-	79.2	-	mJ
			T_j =150°C	-	74.1	-	
$R_{th(j-c)}$	Thermal Resistance, Junction to Case (Diode)			-	0.075	-	°C/W
$R_{th(c-s)}$	Thermal Resistance, Case to sink (Conductive Grease applied)			-	0.025	-	°C/W

Test Conditions

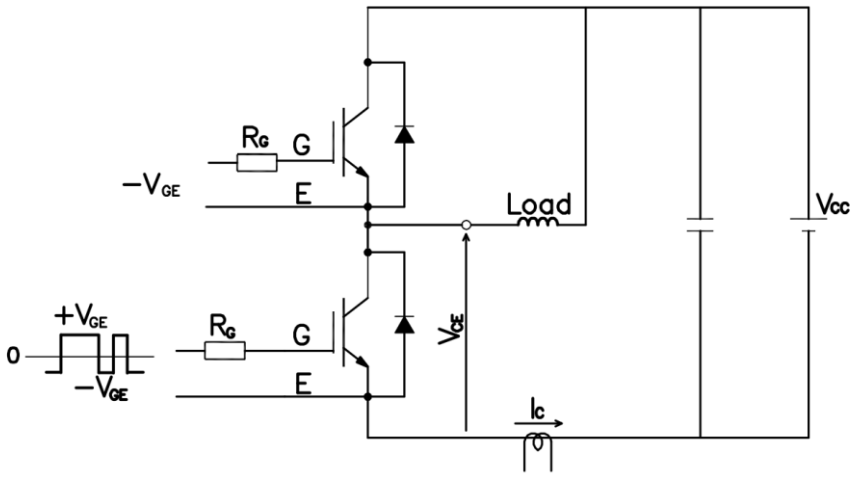

Figure 3. Switching time measure circuit

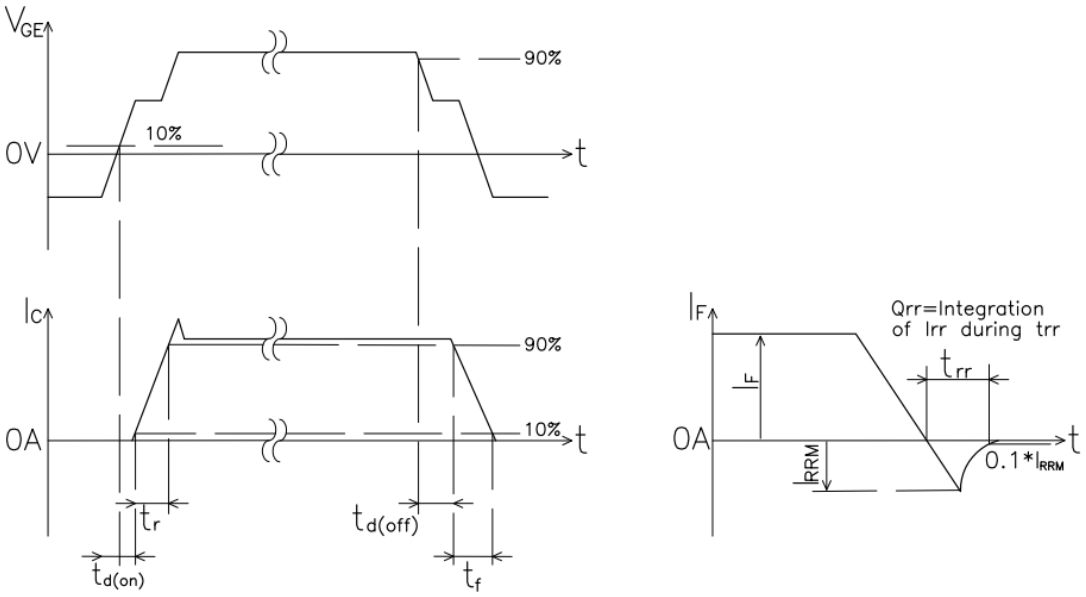

Figure 4. Switching time definition

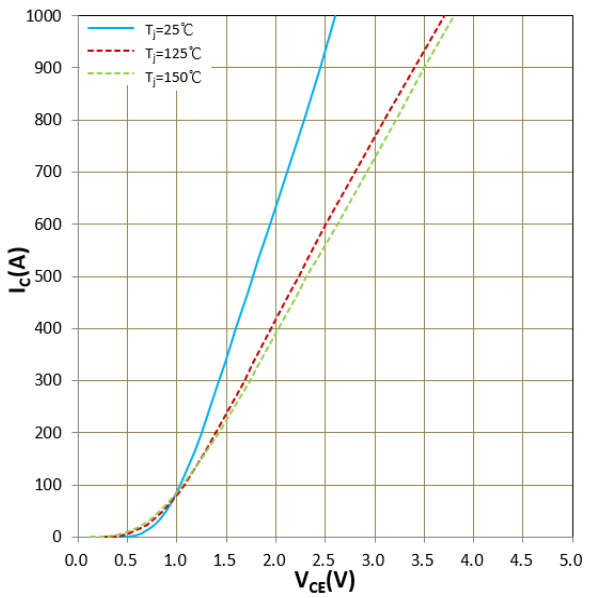

Figure 5. Ic vs V_{CE}
V_{GE} =15V

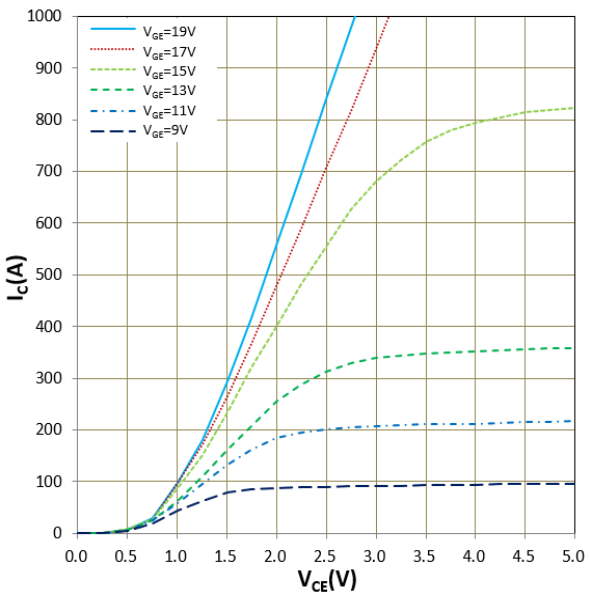

Figure 6. Ic vs V_{CE}
T_j =150°C

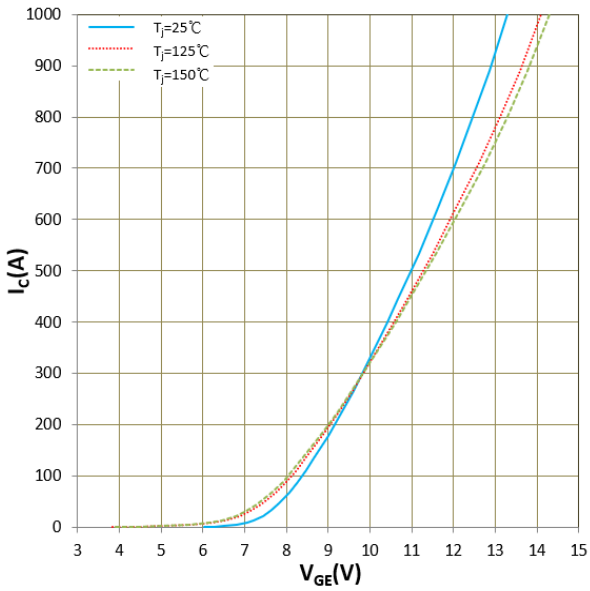

Figure 7. Ic vs V_{GE}
V_{CE} =20V

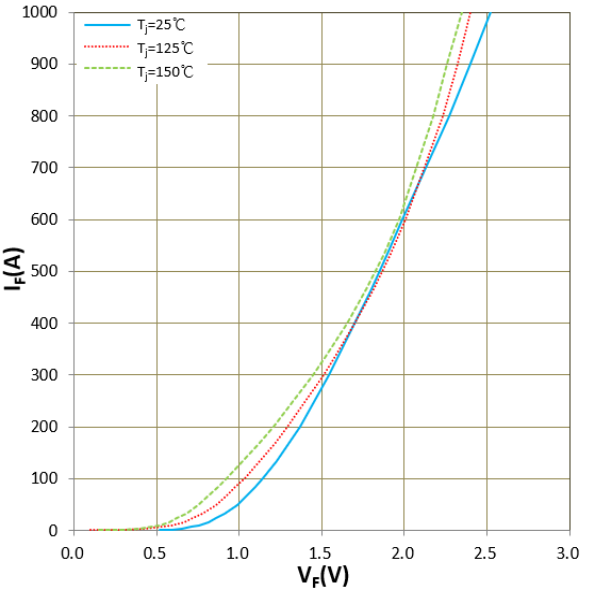

Figure 8. I_F vs V_F

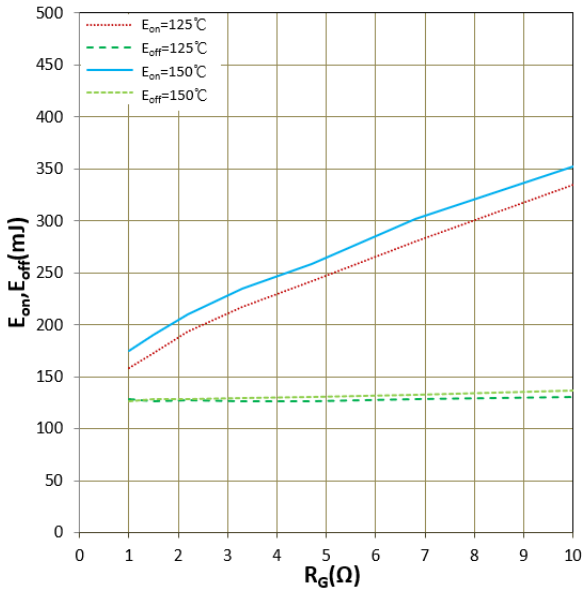

Figure 9. E_{on}, E_{off} vs R_G(Typ)
V_{CC} =900V, V_{GE} =+15V/-8V, I_C = 500A
Inductive Load

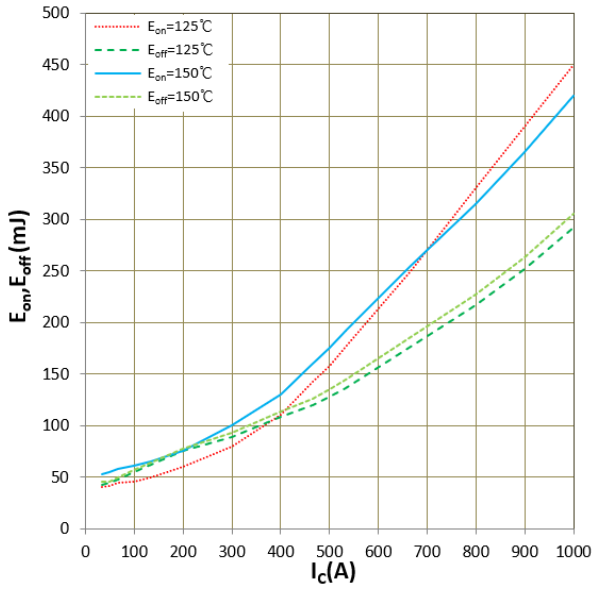

Figure 10 E_{on}, E_{off} vs Ic(Typ)
V_{CC}=900V, V_{GE} =+15V/-8V, R_{Gon} = R_{Goff} =1Ω
Inductive Load

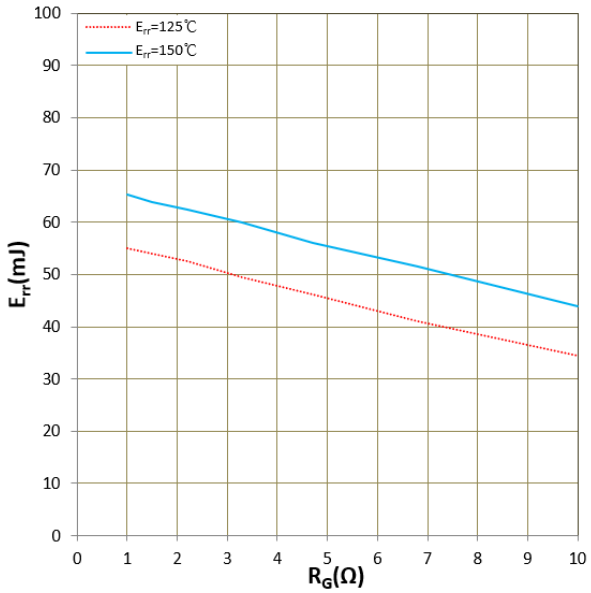

Figure 11. Err vs R_G(Typ)
V_{CC} =900V, V_{GE} =+15V/-8V, I_F =500A
Inductive Load

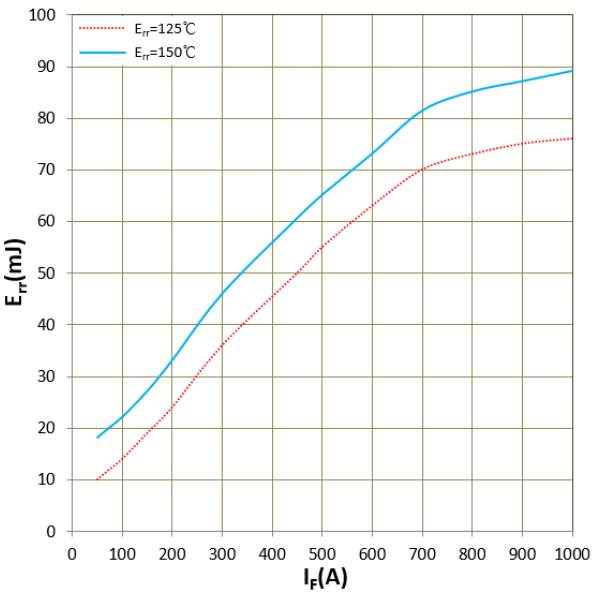

Figure 12. E_{rr} vs I_F(Typ)
V_{CC} =900V, V_{GE} =+15V/-8V, R_{Gon} = R_{Goff} =1Ω
Inductive Load

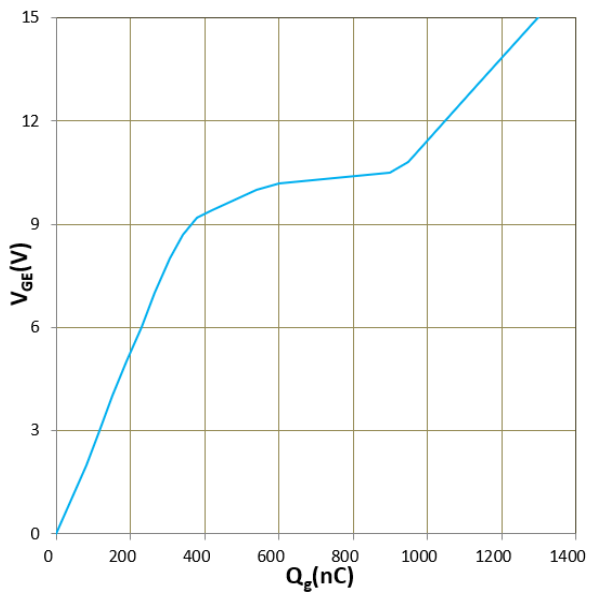

Figure 13. Gate charge

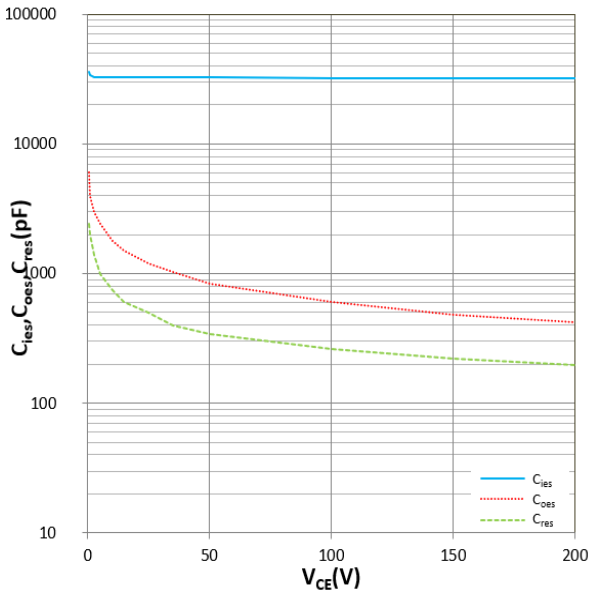

Figure 14. C_{ies}, C_{oes}, C_{res} vs V_{CE}
T_j =25°C, f =1MHz

IMPORTANT NOTICE：

This product data sheet describes the characteristics of this product for which a warranty is granted. Any such warranty is granted exclusively under the terms and conditions of the supply agreement. There will be no guarantee or of any kind for the product and its characteristics.

The data contained in this document is exclusively intended for technically trained staff. You and your technical departments will have to evaluate the product's suitability for the intended application and the completeness of the product data concerning such application.

Due to technical requirements, our product may contain dangerous substances. For information on the types in question, please contact the sales staff responsible for you.

Changes to this product data sheet are reserved.

Please contact the sales staff (Sales@leapers-power.com) for further information on the product, technology, delivery terms, conditions and prices.